

Most Frequently Occurring Classifications of Patents Returned
From A Search of 10049755 on June 25, 2003

Original Classifications

5 430/5
3 430/30
2 118/725
2 216/2
2 361/234
2 378/35
2 430/270.1
2 430/296

Cross-Reference Classifications

8 430/311
3 118/725
3 216/47
3 216/79
3 257/E21.004
3 257/E21.038
3 257/E21.121
3 257/E21.133
3 430/296
3 430/325
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2 118/50.1
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2 219/405
2 219/411
2 250/505.1
2 257/E21.035
2 257/E21.223
2 257/E21.232
2 257/E21.241
2 257/E21.546
2 257/E23.008
2 257/E23.172
2 257/E25.011
2 257/E25.017
2 257/E27.101
2 257/E27.111
2 257/E27.112
2 257/E29.278
2 257/E29.286
2 257/E29.287
2 378/34
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2 430/313
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Combined Classifications

8 430/311
8 430/5
5 118/725
5 430/296
4 216/2
4 378/35
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3 216/47
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3 257/E21.004
3 257/E21.038
3 257/E21.121
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3 430/270.1
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2 118/50.1
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2 361/234
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2 430/269
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Titles of Most Frequently Occurring Classifications of Patents Returned
From A Search of 10049755 on June 25, 2003

8	430/311	(0 OR, 8 XR)
	Class 430 :	RADIATION IMAGERY CHEMISTRY: PROCESS, COMPOSITION, OR PRODUCT THEREOF
	430/269	IMAGING AFFECTING PHYSICAL PROPERTY OF RADIATION SENSITIVE MATERIAL, OR PRODUCING
NONPLANAR OR		
PRODUCT		PRINTING SURFACE - PROCESS, COMPOSITION, OR
	430/311	.Making electrical device
8	430/5	(5 OR, 3 XR)
	Class 430 :	RADIATION IMAGERY CHEMISTRY: PROCESS, COMPOSITION, OR PRODUCT THEREOF
	430/4	RADIATION MODIFYING PRODUCT OR PROCESS OF MAKING
	430/5	.Radiation mask
5	118/725	(2 OR, 3 XR)
	Class 118 :	COATING APPARATUS
	118/715	GAS OR VAPOR DEPOSITION
	118/722	.With treating means (e.g., jarring)
	118/724	..By means to heat or cool
	118/725	...Substrate heater
5	430/296	(2 OR, 3 XR)
	Class 430 :	RADIATION IMAGERY CHEMISTRY: PROCESS, COMPOSITION, OR PRODUCT THEREOF
	430/269	IMAGING AFFECTING PHYSICAL PROPERTY OF RADIATION SENSITIVE MATERIAL, OR PRODUCING
NONPLANAR OR		
PRODUCT		PRINTING SURFACE - PROCESS, COMPOSITION, OR
	430/296	.Electron beam imaging
4	216/2	(2 OR, 2 XR)
	Class 216 :	ETCHING A SUBSTRATE: PROCESSES
	216/2	ETCHING OF SEMICONDUCTOR MATERIAL TO PRODUCE AN ARTICLE HAVING A NONELECTRICAL FUNCTION
4	378/35	(2 OR, 2 XR)
	Class 378 :	X-RAY OR GAMMA RAY SYSTEMS OR DEVICES
	378/1	SPECIFIC APPLICATION
	378/34	.Lithography
	378/35	..Pattern mask
4	430/330	(1 OR, 3 XR)
	Class 430 :	RADIATION IMAGERY CHEMISTRY: PROCESS, COMPOSITION, OR PRODUCT THEREOF
	430/269	IMAGING AFFECTING PHYSICAL PROPERTY OF RADIATION SENSITIVE MATERIAL, OR PRODUCING
NONPLANAR OR		
PRODUCT		PRINTING SURFACE - PROCESS, COMPOSITION, OR
	430/330	.Including heating
3	216/47	(0 OR, 3 XR)

Class 216 : ETCHING A SUBSTRATE: PROCESSES
216/41 MASKING OF A SUBSTRATE USING MATERIAL RESISTANT
TO AN ETCHANT (I.E., ETCH RESIST)
216/47 .Mask is multilayer resist

3 216/79 (0 OR, 3 XR)
Class 216 : ETCHING A SUBSTRATE: PROCESSES
216/58 GAS PHASE ETCHING OF SUBSTRATE
216/74 .Etching inorganic substrate
216/79 ..Etching silicon containing substrate

3 257/E21.004 (0 OR, 3 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE
OR TREATMENT OF SEMICONDUCTOR OR SOLID-
STATE DEVICES OR OF
PARTS THEREOF (EPO)
257/E21.002 .Manufacture or treatment of semiconductor
device (EPO)
257/E21.003 ..Manufacture of two-terminal component for
integrated circuit (EPO)
257/E21.004 ...Of resistor (EPO)

3 257/E21.038 (0 OR, 3 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE
OR TREATMENT OF SEMICONDUCTOR OR SOLID-
STATE DEVICES OR OF
PARTS THEREOF (EPO)
257/E21.002 .Manufacture or treatment of semiconductor
device (EPO)
257/E21.023 ..Making mask on semiconductor body for
further photolithographic processing (EPO)
257/E21.033 ...Comprising inorganic layer (EPO)
257/E21.036Characterized by their size, orientation,
disposition, behavior, shape, in horizontal
or vertical
plane (EPO)
257/E21.038Characterized by process involved to
create mask, e.g., lift-off mask, sidewalls,
or to modify
mask, such as pre-treatment, post-treatment
(EPO)

3 257/E21.121 (0 OR, 3 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE
OR TREATMENT OF SEMICONDUCTOR OR SOLID-
STATE DEVICES OR OF
PARTS THEREOF (EPO)
257/E21.002 .Manufacture or treatment of semiconductor
device (EPO)
257/E21.04 ..Device having at least one potential-jump
barrier or surface barrier, e.g., PN
junction, depletion
layer, carrier concentration layer (EPO)
257/E21.085 ...Device having semiconductor body comprising
Group IV elements or Group III-V compounds
with or without
impurities, e.g., doping materials (EPO)

257/E21.09Deposition of semiconductor material on
substrate, e.g., epitaxial growth, solid
phase epitaxy
(EPO)

257/E21.119Characterized by the substrate (EPO)

257/E21.121Substrate is crystalline insulating
material, e.g., sapphire (EPO)

3 257/E21.133 (0 OR, 3 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE
OR TREATMENT OF SEMICONDUCTOR OR SOLID-
STATE DEVICES OR OF
PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor
device (EPO)

257/E21.04 ..Device having at least one potential-jump
barrier or surface barrier, e.g., PN
junction, depletion
layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising
Group IV elements or Group III-V compounds
with or without
impurities, e.g., doping materials (EPO)

257/E21.09Deposition of semiconductor material on
substrate, e.g., epitaxial growth, solid
phase epitaxy
(EPO)

257/E21.133Epitaxial re-growth of non-monocrystalline
semiconductor material, e.g., lateral epitaxy
by seeded
solid-state
solidification, solid-state crystallization,
graphoepitaxy, explosive crystallization,
grain growth in
polycrystalline material (EPO)

3 430/270.1 (2 OR, 1 XR)
Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF
430/269 IMAGING AFFECTING PHYSICAL PROPERTY OF
RADIATION SENSITIVE MATERIAL, OR PRODUCING
NONPLANAR OR
PRINTING SURFACE - PROCESS, COMPOSITION, OR
PRODUCT

430/270.1 .Radiation sensitive composition or product or
process of making

3 430/30 (3 OR, 0 XR)
Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF
430/30 INCLUDING CONTROL FEATURE RESPONSIVE TO A TEST
OR MEASUREMENT

3 430/313 (1 OR, 2 XR)
Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF
430/269 IMAGING AFFECTING PHYSICAL PROPERTY OF
RADIATION SENSITIVE MATERIAL, OR PRODUCING
NONPLANAR OR

PRINTING SURFACE - PROCESS, COMPOSITION, OR

PRODUCT

430/311 .Making electrical device

430/313 ..With formation of resist image, and etching
of substrate or material deposition

3 430/325 (0 OR, 3 XR)

Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF

430/269 IMAGING AFFECTING PHYSICAL PROPERTY OF
RADIATION SENSITIVE MATERIAL, OR PRODUCING

NONPLANAR OR

PRINTING SURFACE - PROCESS, COMPOSITION, OR

PRODUCT

430/322 .Forming nonplanar surface

430/325 ..Post image treatment to produce elevated
pattern

3 430/966 (0 OR, 3 XR)

Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF

430/966 X-RAY

2 118/50.1 (0 OR, 2 XR)

Class 118 : COATING APPARATUS
118/50 WITH VACUUM OR FLUID PRESSURE CHAMBER

118/50.1 .With means to apply electrical and/or radiant
energy to work and/or coating material

2 118/500 (1 OR, 1 XR)

Class 118 : COATING APPARATUS
118/500 WORK HOLDERS, OR HANDLING DEVICES

2 118/728 (0 OR, 2 XR)

Class 118 : COATING APPARATUS
118/715 GAS OR VAPOR DEPOSITION

118/728 .Work support

2 118/729 (0 OR, 2 XR)

Class 118 : COATING APPARATUS
118/715 GAS OR VAPOR DEPOSITION

118/728 .Work support

118/729 ..Moving work support

2 118/730 (0 OR, 2 XR)

Class 118 : COATING APPARATUS
118/715 GAS OR VAPOR DEPOSITION

118/728 .Work support

118/729 ..Moving work support

118/730 ...Rotary

2 156/345.51 (1 OR, 1 XR)

Class 156 : ADHESIVE BONDING AND MISCELLANEOUS CHEMICAL
MANUFACTURE

156/345.1 DIFFERENTIAL FLUID ETCHING APPARATUS

156/345.51 .With workpiece support

2 216/12 (0 OR, 2 XR)

Class 216 : ETCHING A SUBSTRATE: PROCESSES
216/12 FORMING OR TREATING MASK USED FOR ITS

NONETCHING FUNCTION (E.G., SHADOW MASK, X-RAY
MASK, ETC.)

- 2 216/67 (0 OR, 2 XR)
Class 216 : ETCHING A SUBSTRATE: PROCESSES
216/58 GAS PHASE ETCHING OF SUBSTRATE
216/63 .Application of energy to the gaseous etchant
or to the substrate being etched
216/67 ..Using plasma
- 2 216/99 (0 OR, 2 XR)
Class 216 : ETCHING A SUBSTRATE: PROCESSES
216/83 NONGASEOUS PHASE ETCHING OF SUBSTRATE
216/96 .Etching inorganic substrate
216/99 ..Substrate contains silicon or silicon
compound
- 2 219/405 (0 OR, 2 XR)
Class 219 : ELECTRIC HEATING
219/260 .Resistive element: igniter type
219/385 .Combined with container, enclosure, or support
for material to be heated
219/391 ..Oven type
219/402 ...With casing or support for heating unit or
units
219/405Including heat energy reflecting or
directing means
- 2 219/411 (0 OR, 2 XR)
Class 219 : ELECTRIC HEATING
219/260 .Resistive element: igniter type
219/385 .Combined with container, enclosure, or support
for material to be heated
219/391 ..Oven type
219/409 ...With heating unit structure or composition
219/411With infrared generating means
- 2 250/505.1 (0 OR, 2 XR)
Class 250 : RADIANT ENERGY
250/505.1 RADIATION CONTROLLING MEANS
- 2 257/E21.035 (0 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE
OR TREATMENT OF SEMICONDUCTOR OR SOLID-
STATE DEVICES OR OF
PARTS THEREOF (EPO)
257/E21.002 .Manufacture or treatment of semiconductor
device (EPO)
257/E21.023 ..Making mask on semiconductor body for
further photolithographic processing (EPO)
257/E21.033 ...Comprising inorganic layer (EPO)
257/E21.035Characterized by their composition, e.g.,
multilayer masks, materials (EPO)
- 2 257/E21.223 (0 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE

OR TREATMENT OF SEMICONDUCTOR OR

SOLID-STATE DEVICES OR OF

PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor device (EPO)

257/E21.04 ..Device having at least one potential-jump barrier or surface barrier, e.g., PN junction, depletion layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising Group IV elements or Group III-V compounds with or without impurities, e.g., doping materials (EPO)

257/E21.211Treatment of semiconductor body using process other than deposition of semiconductor material on a substrate, diffusion or alloying of impurity material, or radiation treatment (EPO)

257/E21.214To change their surface-physical characteristics or shape, e.g., etching, polishing, cutting (EPO)

257/E21.215Chemical or electrical treatment, e.g., electrolytic etching (EPO)

257/E21.219Chemical etching (EPO)

257/E21.223Anisotropic liquid etching (EPO)

2 257/E21.232 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE OR TREATMENT OF SEMICONDUCTOR OR

SOLID-STATE DEVICES OR OF

PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor device (EPO)

257/E21.04 ..Device having at least one potential-jump barrier or surface barrier, e.g., PN junction, depletion layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising Group IV elements or Group III-V compounds with or without impurities, e.g., doping materials (EPO)

257/E21.211Treatment of semiconductor body using process other than deposition of semiconductor material on a substrate, diffusion or alloying of impurity material, or radiation treatment (EPO)

257/E21.214To change their surface-physical characteristics or shape, e.g., etching, polishing, cutting (EPO)

257/E21.215Chemical or electrical treatment, e.g., electrolytic etching (EPO)

257/E21.231Using mask (EPO)

257/E21.232Characterized by their composition,

e.g., multilayer masks, materials (EPO)

2 257/E21.241 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE
OR TREATMENT OF SEMICONDUCTOR OR

SOLID-STATE DEVICES OR OF

PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor
device (EPO)

257/E21.04 ..Device having at least one potential-jump
barrier or surface barrier, e.g., PN

junction, depletion

layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising
Group IV elements or Group III-V

compounds with or without

impurities, e.g., doping materials (EPO)

257/E21.211Treatment of semiconductor body using
process other than deposition of

semiconductor material on

a substrate, diffusion or alloying of

impurity material, or

radiation treatment (EPO)

257/E21.214To change their surface-physical
characteristics or shape, e.g., etching,

polishing, cutting

(EPO)

257/E21.24To form insulating layer thereon, e.g.,
for masking or by using photolithographic

technique (EPO)

257/E21.241Post-treatment (EPO)

2 257/E21.546 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.531 ...For electrical parameters, e.g.,
resistance, deep-levels, CV, diffusions

by electrical means

(EPO)

257/E21.532 .Manufacture or treatment of devices
consisting of plurality of solid state

components formed in

or on common substrate or of parts

thereof; manufacture of

integrated circuit devices or of parts

thereof (EPO)

257/E21.536 ..Manufacture of specific parts of devices
(EPO)

257/E21.54 ...Making of isolation regions between
components (EPO)

257/E21.545Dielectric regions, e.g., EPIC dielectric
isolation, LOCOS; trench refilling

techniques, SOI

technology, use of channel stoppers (EPO)

257/E21.546Using trench refilling with dielectric
materials (EPO)

2 257/E23.008 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E23.001 PACKAGING, INTERCONNECTS, AND MARKINGS FOR
SEMICONDUCTOR OR OTHER SOLID-STATE DEVICES
(EPO)

257/E23.003 .Mountings, e.g., nondetachable insulating
substrates (EPO)

257/E23.005 ..Characterized by material or its electrical
properties (EPO)

257/E23.008 ...Semiconductor insulating substrates (EPO)

2 257/E23.172 (0 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES

257/E23.139 ...Liquid at normal operating temperature of
device (EPO)

257/E23.141 .Arrangements for conducting electric current
within device in operation from one
component to another,
interconnections, e.g., wires, lead frames
(EPO)

257/E23.169 ..Interconnection structure between plurality
of semiconductor chips being formed on or in
insulating
substrates (EPO)

257/E23.172 ...Assembly of plurality of insulating
substrates (EPO)

2 257/E25.011 (0 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES

257/E25.001 ASSEMBLIES CONSISTING OF PLURALITY OF
INDIVIDUAL SEMICONDUCTOR OR OTHER SOLID-
STATE DEVICES (EPO)

257/E25.002 .All devices being of same type, e.g.,
assemblies of rectifier diodes (EPO)

257/E25.003 ..Devices not having separate containers (EPO)

257/E25.01 ...Device consisting of plurality of
semiconductor or other solid state devices
or components
formed in or on common substrate, e.g.,
integrated circuit
device (EPO)

257/E25.011Devices being arranged next and on each
other, i.e., mixed assemblies (EPO)

2 257/E25.017 (0 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES

257/E25.001 ASSEMBLIES CONSISTING OF PLURALITY OF
INDIVIDUAL SEMICONDUCTOR OR OTHER SOLID-
STATE DEVICES (EPO)

257/E25.002 .All devices being of same type, e.g.,
assemblies of rectifier diodes (EPO)

257/E25.003 ..Devices not having separate containers (EPO)

257/E25.014 ...Semiconductor devices adapted for
rectifying, amplifying, oscillating, or
switching,
capacitors, or resistors with at least one
potential-jump
barrier or surface barrier (EPO)

257/E25.017Apertured devices mounted on one or more rods passed through apertures (EPO)

2 257/E27.101 (0 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E27.006 .Including piezo-electric, electro-resistive, or magneto-resistive component (EPO)
257/E27.009 .Including semiconductor component with at least one potential barrier or surface barrier adapted for rectifying, oscillating, amplifying, or switching, or Including integrated passive circuit elements (EPO)
257/E27.01 ..With semiconductor substrate only (EPO)
257/E27.07 ...Including a plurality of individual components in a repetitive configuration (EPO)
257/E27.081Including field-effect component (EPO)
257/E27.098Static random access memory, SRAM, structure (EPO)
257/E27.101Load element being a resistor (EPO)

2 257/E27.111 (0 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E27.006 .Including piezo-electric, electro-resistive, or magneto-resistive component (EPO)
257/E27.009 .Including semiconductor component with at least one potential barrier or surface barrier adapted for rectifying, oscillating, amplifying, or switching, or Including integrated passive circuit elements (EPO)
257/E27.111 ..Substrate comprising other than a semiconductor material, e.g. insulating substrate or layered substrate Including a non-semiconductor layer (EPO)

2 257/E27.112 (0 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E27.006 .Including piezo-electric, electro-resistive, or magneto-resistive component (EPO)
257/E27.009 .Including semiconductor component with at least one potential barrier or surface barrier adapted for rectifying, oscillating, amplifying, or switching, or Including integrated passive circuit elements (EPO)
257/E27.111 ..Substrate comprising other than a semiconductor material, e.g. insulating substrate or layered substrate Including a non-semiconductor layer (EPO)
257/E27.112 ...Including insulator on semiconductor, e.g. SOI (silicon on insulator) (EPO)

2 257/E29.278 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E29.162Insulating materials for IGFET (EPO)

257/E29.166 .Types of semiconductor device (EPO)

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257/E29.168 ..types of semiconductor
257/E29.169 ..Controllable by only signal applied to
                control electrode (e.g., base of

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bipolar transistor, gate

of field-effect transistor) (EPO)

257/E29.226 ...Unipolar device (EPO)

257/E29.242Field effect transistor (EPO)

257/E29.255With field effect produced by insulated gate (EPO)

257/E29.273Thin film-transistor (EPO)

257/E29.276With supplementary region or layer in
thin film or in insulated bulk substrate

supporting it for

controlling or increasing voltage

resistance of device

(EPO)

257/E29.277Characterized by drain or source
properties (EPO)

257/E29.278With LDD structure or extension or
offset region or characterized by doping

profile (EPO)

2 257/E29.286 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E29.162Insulating materials for IGFET (EPO)

257/E29 166 .Types of semiconductor device (EPO)

257/E29.169 ..Controllable by only signal applied to
control electrode (e.g., base of

bipolar transistor, gate

of field-effect transistor) (EPO)

257/E29.226 ...Unipolar device (EPO)

257/E29.242Field effect transistor (EPO)

257/E29.242With field effect produced by insulated
257/E29.255gate (EPO)

257/E29.273Thin film-transistor (EPO)

257/F29.285Silicon transistor (EPO)

257/E29.286Monocrystalline only (EPO)

2 257/E29.287 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E29.162Insulating materials for IGFET (EPO)

257/E29.166 Types of semiconductor device (EPO)

257/E29.168 ..types of semiconductor
257/E29.169 ..Controllable by only signal applied to
control electrode (e.g., base of

bipolar transistor, gate

of field-effect transistor) (EPO)

257/E29.226 ...Unipolar device (EPO)

257/E29.242Field effect transistor (EPO)

257/E29.242With field effect produced by insulated
257/E29.255date (EPO)

257/E29.273Thin film-transistor (EPO)

257/E29.285Silicon transistor (EPO)

257/E29.286Monocrystalline only (EPO)

257/E29.287 SOS transistor (EPO)

2 361/234

(2 OR, 0 XR)

Class 361 : ELECTRICITY: ELECTRICAL SYSTEMS AND DEVICES

361/230 ELECTRIC CHARGE GENERATING OR CONDUCTING MEANS
(E.G., CHARGING OF GASES)

361/233 .Use of forces of electric charge or field

361/234 ..Pinning

2 378/34 (0 OR, 2 XR)

Class 378 : X-RAY OR GAMMA RAY SYSTEMS OR DEVICES

378/1 SPECIFIC APPLICATION

378/34 .Lithography

2 392/416 (1 OR, 1 XR)

Class 392 : ELECTRIC RESISTANCE HEATING DEVICES

392/407 .Radiant heater

392/416 ..With chamber

2 430/269 (0 OR, 2 XR)

Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF

430/269 IMAGING AFFECTING PHYSICAL PROPERTY OF
RADIATION SENSITIVE MATERIAL, OR PRODUCING
NONPLANAR OR
PRINTING SURFACE - PROCESS, COMPOSITION, OR
PRODUCT

2 430/323 (0 OR, 2 XR)

Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF

430/269 IMAGING AFFECTING PHYSICAL PROPERTY OF
RADIATION SENSITIVE MATERIAL, OR PRODUCING
NONPLANAR OR
PRINTING SURFACE - PROCESS, COMPOSITION, OR
PRODUCT

430/322 .Forming nonplanar surface

430/323 ..Including etching substrate

2 430/324 (0 OR, 2 XR)

Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF

430/269 IMAGING AFFECTING PHYSICAL PROPERTY OF
RADIATION SENSITIVE MATERIAL, OR PRODUCING
NONPLANAR OR
PRINTING SURFACE - PROCESS, COMPOSITION, OR
PRODUCT

430/322 .Forming nonplanar surface

430/324 ..Including material deposition

2 430/942 (0 OR, 2 XR)

Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF

430/942 ELECTRON BEAM

2 430/967 (0 OR, 2 XR)

Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF

430/966 X-RAY

430/967 .X-ray exposure process

2 438/703 (0 OR, 2 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/689 CHEMICAL ETCHING

438/694 .Combined with coating step

438/703 ..Plural coating steps

2 438/928 (0 OR, 2 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/928 FRONT AND REAR SURFACE PROCESSING